The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for testing comprising:

irradiating a visible light on a surface of a semiconductor film, of which a crystallinity is improved by irradiating an energy beam;

photographing a scattered light of the irradiated visible light; and

digitalizing the photographed image to make a digital image,

wherein a direction in which the energy beam is scanned is a Y direction, and a direction perpendicular to the Y direction is an X direction in the digital image;

sectioning m x n basic units by dividing the digital image into m along the X direction and into n along the Y direction in a predetermined analysis in the digital image;

calculating an average value ~~or a sum~~ of a corrected saturation of the n basic units aligned in the X directions per each of the m rows aligned in the Y direction; and

obtaining an approximate line from a relation of [[an]] a position in the Y direction to the average value ~~or the sum~~ corresponding to the position in the Y direction; and

testing the crystallinity of the semiconductor film, of which the crystallinity is improved, with a fluctuation obtained from the approximate line, and the average value ~~or the sum~~.

2. (Canceled)

3. (Currently Amended) A method for testing comprising:

irradiating a visible light on a surface of a semiconductor film, of which a crystallinity is improved by irradiating an energy beam;

photographing a scattered light of the irradiated visible light; and

digitalizing the photographed image to make a digital image,

wherein a direction in which the energy beam is scanned is a Y direction, and a direction perpendicular to the Y direction is an X direction in the digital image;

sectioning m x n basic units by dividing the digital image into m along the X direction and n along the Y direction in a predetermined analysis in the digital image;

calculating an average value ~~or a sum~~ of luminance of the n basic units aligned in the X directions per each of the m rows aligned in the Y direction;

obtaining an approximate line from a relation of a position in the Y direction to the average value corresponding to the position in the Y direction; and

testing the crystallinity of the semiconductor film, of which the crystallinity is improved, with a fluctuation obtained from the approximate line, and the average value ~~or the sum~~.

4.-10. (Canceled)

11. (Previously Presented) The method for testing according to claim 1, wherein the crystallinity of the semiconductor film is tested by using an average luminance of the digital image.

12. (Canceled)

13. (Previously Presented) The method for testing according to claim 3, wherein the crystallinity of the semiconductor film is tested by further using an average luminance of the digital image.

14.-15. (Canceled)

16. (Previously Presented) The method for testing according to claim 1, wherein the crystallinity of the semiconductor film is tested by further using an average corrected saturation in the digital image.

17. (Canceled)

18. (Previously Presented) The method for testing according to claim 3, wherein the crystallinity of the semiconductor film is tested by further using an average corrected saturation in the digital image.

19.-25. (Canceled)

26. (Currently Amended) A method for testing a beam profile comprising:

irradiating an energy beam of one pulse on a substrate over which an amorphous semiconductor film is formed;

irradiating a visible light on a surface of the substrate and photographing scattered light of the irradiated visible light;

digitalizing the photographed image to make a digital image,

wherein a direction in which the energy beam is scanned is a Y direction, and a direction perpendicular to the Y direction is an X direction in the digital image;

sectioning m x n basic units by dividing the digital image into m along the X direction and n along the Y direction in a predetermined analysis in the digital image;

calculating an average value ~~or a sum~~ of a corrected saturation of the m basic units aligned in the X directions per each of the m rows aligned in the Y direction;

obtaining an approximate line from a relation of a position in the Y direction to the average value ~~or the sum~~ corresponding to the position in the Y direction; and

testing a crystallinity of the semiconductor film, of which the crystallinity is improved, with a fluctuation obtained from the approximate line, and the average value ~~or the sum~~.

27. (Canceled)

28. (Currently Amended) A method for testing a beam profile comprising:

irradiating an energy beam of one pulse on a substrate over which an amorphous semiconductor film is formed;

irradiating a visible light on a surface of the substrate and photographing scattered light of the irradiated visible light; and

wherein a direction in which the energy beam is scanned is a Y direction, and a direction perpendicular to the Y direction is an X direction in the digital image;

sectioning m x n basic units by dividing the digital image into m along the X direction and n along the Y direction in a predetermined analysis in the digital image;

calculating an average value ~~or a sum~~ of luminance of the m basic units aligned in the X directions per each of the m rows aligned in the Y direction;

obtaining an approximate line from a relation of a position in the Y direction to the average value corresponding to the position in the Y direction; and

testing a crystallinity of the semiconductor film, of which the crystallinity is improved, with a fluctuation obtained from the approximate line, and the average value ~~or the sum~~.

29.-31. (Canceled)

32. (Original) The method for testing according to claim 1, wherein the energy beam is a laser light.

33. (Canceled)

34. (Original) The method for testing according to claim 3, wherein the energy beam is a laser light.

35.-36. (Canceled)

37. (Previously Presented) The method for testing according to claim 1, wherein the visible light is irradiated from a light source selected from the group consisting of a metal halide lamp, a halogen lamp, a tungsten lamp, a xenon lamp, a light emitting diode, and a fluorescent lamp.

38. (Canceled)

39. (Previously Presented) The method for testing according to claim 3, wherein the visible light is irradiated from a light source selected from the group consisting of a metal halide lamp, a halogen lamp, a tungsten lamp, a xenon lamp, a light emitting diode, and a fluorescent lamp.

40.-41. (Canceled)

42. (Previously Presented) The method for testing according to claim 26, wherein the visible light is irradiated from a light source selected from the group consisting of a metal halide lamp, a halogen lamp, a tungsten lamp, a xenon lamp, a light emitting diode, and a fluorescent lamp.

43. (Canceled)

44. (Previously Presented) The method for testing according to claim 28, wherein the visible light is irradiated from a light source selected from the group consisting of a metal halide lamp, a halogen lamp, a tungsten lamp, a xenon lamp, a light emitting diode, and a fluorescent lamp.

45. (Previously Presented) The method for testing according to claim 1, wherein an illumination intensity of the visible light irradiating on a surface of the semiconductor film is 10,000 lux or more.

46. (Canceled)

47. (Previously Presented) The method for testing according to claim 3, wherein an illumination intensity of the visible light irradiating on a surface of the semiconductor film is 10,000 lux or more.

48.-49. (Canceled)

50. (Previously Presented) The method for testing according to claim 26, wherein an illumination intensity of the visible light irradiating on a surface of the semiconductor film is 10,000 lux or more.

51. (Canceled)

52. (Previously Presented) The method for testing according to claim 28, wherein an illumination intensity of the visible light irradiating on a surface of the semiconductor film is 10,000 lux or more.

53. (Original) The method for testing according to claim 45, wherein the illumination intensity is from 20,000 to 100,000 lux.

54. (Canceled)

55. (Original) The method for testing according to claim 47, wherein the illumination intensity is from 20,000 to 100,000 lux.

56.-57. (Canceled)

58. (Original) The method for testing according to claim 50, wherein the illumination intensity is from 20,000 to 100,000 lux.

59. (Canceled)

60. (Original) The method for testing according to claim 52, wherein the illumination intensity is from 20,000 to 100,000 lux.

61.-68. (Canceled)

69. (Previously Presented) A manufacturing method of a semiconductor device, comprising:

testing each of a plurality of semiconductor films crystallized by an energy beam having a different density by the method for testing according to claim 1; and

determining an irradiation energy density by a result of a test to crystallize the semiconductor film.

70. (Canceled)

71. (Previously Presented) A manufacturing method of a semiconductor device, comprising:

testing each of a plurality of semiconductor films crystallized by an energy beam having a different density by the method for testing according to claim 3; and

determining an irradiation energy density by a result of a test to crystallize the semiconductor film.

72.-73. (Canceled)

74. (Previously Presented) A manufacturing method of a semiconductor device, comprising:

testing each of a plurality of semiconductor films crystallized by an energy beam having a different density by the method for testing according to claim 26; and

determining an irradiation energy density by a result of a test to crystallize the semiconductor film.

75. (Canceled)

76. (Previously Presented) A manufacturing method of a semiconductor device, comprising:

testing each of a plurality of semiconductor films crystallized by an energy beam having a different density by the method for testing according to claim 28; and

determining an irradiation energy density by a result of a test to crystallize the semiconductor film.

77. (Original) The manufacturing method according to claim 69, wherein a means for photographing the scattered light is provided in a crystallization chamber.

78. (Canceled)

79. (Original) The manufacturing method according to claim 71, wherein a means for photographing the scattered light is provided in a crystallization chamber.

80.-81. (Canceled)

82. (Original) The manufacturing method according to claim 74, wherein a means for photographing the scattered light is provided in a crystallization chamber.

83. (Previously Presented) The manufacturing method according to claim 77, wherein a means for photographing the scattered light is provided in a crystallization chamber.

84.-85. (Canceled)